

PNP MJ2500 - MJ2501

COMPLEMENTARY POWER DARLINGTONS

The MJ2500, and MJ2501 are silicon epitaxial-base PNP power transistors in monolithic Darlington configuration and are mounted in Jedec TO-3 metal case. They are intented for use in power linear and switching applications.

The complementary NPN types are the MJ3000 and MJ3001 respectively Compliance to RoHS

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings			Value	Unit
V _{CBO}	Collector-Base Voltage	I _E =0	MJ2500	-60	V
			MJ2501	-80	V
V _{CEO}	Collector-EmitterVoltage	I _B =0	MJ2500	-60	V
			MJ2501	-80	V
V _{EBO}	Emitter-Base Voltage	I _C =0	MJ2500	-5.0	V
			MJ2501		
	Collector Current		MJ2500	10	Λ
Ic	Collector Current		MJ2501	-10	A
I _B	Base Current		MJ2500	0.0	А
			MJ2501	-0.2	
P _T	Power Dissipation	1(0) 1 ₂ - 25° -	MJ2500	150	W
			MJ2501		
TJ	Junction Temperature		MJ2500	200	8
T _s	Storage Temperature		MJ2501	-65 to +200	C

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R _{thJ-C}	Thermal Resistance, Junction to Case 1.17 ℃/		℃/W



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ELECTRICAL CHARACTERISTICS

TC=25℃ unless otherwise noted

Symbol	Ratings	Test Cond	lition(s)	Min	Тур	Max	Unit
BV _{CEO}	Collector-Emitter Breakdown	I _C =-100mA	MJ2500	-60	-	-	V
PACEO	Voltage (*)	I _B =0	MJ2501	-80	-	-	V
I _{CEO}	Collector Cutoff Current	V_{CE} =-30 V I_{B} =0	MJ2500	-	-	-1.0	mA
		V_{CE} =-40 V I_{B} =0	MJ2501	-	-		
I _{EBO}	Emitter Cutoff Current	V _{BE} =-5.0 V	MJ2500		-	-2.0	mA
		$I_{C}=0$	MJ2501	-			
	Collector-Emitter Leakage Current	V _{CB} =-60 V	MJ2500	-	-	-1.0	mA
		$R_{BE}=1.0 \text{ k}\Omega$	10132300				
		V _{CB} =-80 V	MJ2501	-	_		
		$R_{BE}=1.0 \text{ k}\Omega$	10102301		_		
loss		V _{CB} =-60 V		-	-	-5.0	
I _{CER}		$R_{BE}=1.0 \text{ k}\Omega$	MJ2500				
		T _C =150℃					
		V _{CB} =-80 V		-	-		
		$R_{BE}=1.0 k\Omega$	MJ2501				
		T _C =150℃					
V _{CE(SAT)}	Collector-Emitter saturation Voltage (*)	I _C =-5.0 A	MJ2500	_	-	-2.0	V
		$I_B=-20 \text{ mA}$	MJ2501				
		I _C =-10 A	MJ2500	_	-	-4.0	
		$I_B=-50 \text{ mA}$	MJ2501				
V	Base-Emitter Voltage (*)	I _C =-5.0 A	MJ2500	_	-	-3	V
V _{BE}		V _{CE} =-3.0V	MJ2501				
h	DC Current Gain (*)	V _{CE} =-3.0 V	MJ2500	1000	-	-	-
h _{FE}		I_{C} =-5.0 A	MJ2501	1000			

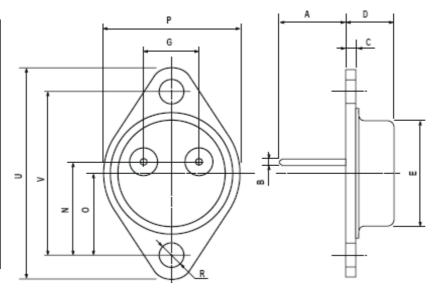
^(*) Pulse Width \approx 300 μ s, Duty Cycle \angle 2.0%



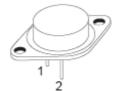
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)				
	min	max		
A	11	13.10		
В	0.97	1.15		
С	1.5	1.65		
D	8.32	8.92		
F	19	20		
G	10.70	11.1		
N	16.50	17.20		
Р	25	26		
R	4	4.09		
U	38.50	39.30		
V	30	30.30		



Pin 1 :	Base
Pin 2 :	Emitter
Case:	Collector



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